

Manuel Cardona

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

196
papers

18,549
citations

63
h-index

134
g-index

200
ext. papers

19,623
ext. citations

3.3
avg, IF

6.35
L-index

#	Paper	IF	Citations
196	Infrared and Raman spectra of the silicon-hydrogen bonds in amorphous silicon prepared by glow discharge and sputtering. <i>Physical Review B</i> , 1977 , 16, 3556-3571	3.3	1477
195	Piezo-Electroreflectance in Ge, GaAs, and Si. <i>Physical Review</i> , 1968 , 172, 816-837		798
194	Stress-Induced Shifts of First-Order Raman Frequencies of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1972 , 5, 580-593	3.3	779
193	Fundamentals of Semiconductors 1996 ,		733
192	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review</i> , 1967 , 154, 696-720		715
191	Resonant Raman scattering in ZnO. <i>Physical Review B</i> , 1977 , 16, 3753-3761	3.3	707
190	Optical Properties and Band Structure of SrTiO ₃ and BaTiO ₃ . <i>Physical Review</i> , 1965 , 140, A651-A655		661
189	Temperature dependence of the first-order Raman scattering by phonons in Si, Ge, and Sn: Anharmonic effects. <i>Physical Review B</i> , 1984 , 29, 2051-2059	3.3	619
188	Energy-Band Structure of Germanium and Silicon: The k Method. <i>Physical Review</i> , 1966 , 142, 530-543		550
187	Optical Properties of the Silver and Cuprous Halides. <i>Physical Review</i> , 1963 , 129, 69-78		538
186	Acoustic deformation potentials and heterostructure band offsets in semiconductors. <i>Physical Review B</i> , 1987 , 35, 6182-6194	3.3	489
185	Optical Properties and Band Structure of Wurtzite-Type Crystals and Rutile. <i>Physical Review</i> , 1965 , 137, A1467-A1476		474
184	Band parameters of semiconductors with zincblende, wurtzite, and germanium structure. <i>Journal of Physics and Chemistry of Solids</i> , 1963 , 24, 1543-1555	3.9	401
183	Optical Properties and Band Structure of Group IV-VI and Group V Materials. <i>Physical Review</i> , 1964 , 133, A1685-A1697		359
182	Isotope effects on the optical spectra of semiconductors. <i>Reviews of Modern Physics</i> , 2005 , 77, 1173-1224	40.5	319
181	Dependence of the direct energy gap of GaAs on hydrostatic pressure. <i>Physical Review B</i> , 1975 , 12, 5729-5738	3.5	287
180	Fundamental Reflectivity and Band Structure of ZnTe, CdTe, and HgTe. <i>Physical Review</i> , 1963 , 131, 98-103		255

179	Thermoreflectance in Semiconductors. <i>Physical Review</i> , 1968 , 176, 950-960		227
178	Effects of Uniaxial Stress on the Indirect Exciton Spectrum of Silicon. <i>Physical Review B</i> , 1971 , 3, 2623-2636		218
177	Densities of valence states of amorphous and crystalline III-V and II-VI semiconductors. <i>Physical Review B</i> , 1974 , 9, 2627-2648	3.3	210
176	Effect of Carrier Concentration on the Raman Frequencies of Si and Ge. <i>Physical Review B</i> , 1972 , 5, 1440-1454	3.3	194
175	Electron Effective Masses of InAs and GaAs as a Function of Temperature and Doping. <i>Physical Review</i> , 1961 , 121, 752-758		175
174	Raman scattering in pure and hydrogenated amorphous germanium and silicon. <i>Journal of Non-Crystalline Solids</i> , 1979 , 32, 405-419	3.9	174
173	Pressure dependence of Raman phonons of Ge and 3C-SiC. <i>Physical Review B</i> , 1982 , 25, 1151-1160	3.3	160
172	Modulated Piezoreflectance in Semiconductors. <i>Physical Review B</i> , 1970 , 1, 672-682	3.3	160
171	Photoluminescence in heavily doped GaAs. I. Temperature and hole-concentration dependence. <i>Physical Review B</i> , 1980 , 22, 886-893	3.3	156
170	Fundamental Reflectivity Spectrum of Semiconductors with Zinc-Blende Structure. <i>Journal of Applied Physics</i> , 1961 , 32, 2151-2155	2.5	154
169	Electroreflectance in the GaAs-GaP Alloys. <i>Physical Review</i> , 1966 , 146, 601-610		153
168	Interference effects: A key to understanding forbidden Raman scattering by LO phonons in GaAs. <i>Physical Review B</i> , 1985 , 31, 3696-3704	3.3	152
167	Absorption Spectrum of Germanium and Zinc-Blende-Type Materials at Energies Higher than the Fundamental Absorption Edge. <i>Journal of Applied Physics</i> , 1963 , 34, 813-818	2.5	148
166	Intrinsic Piezobirefringence of Ge, Si, and GaAs. <i>Physical Review</i> , 1969 , 184, 821-829		144
165	Bond Charge, Bond Polarizability, and Phonon Spectra in Semiconductors. <i>Physical Review Letters</i> , 1975 , 34, 580-583	7.4	131
164	First- and second-order Raman spectra of galena (PbS). <i>Journal of Applied Physics</i> , 2002 , 92, 4375-4380	2.5	126
163	Electron-phonon interaction in tetrahedral semiconductors. <i>Solid State Communications</i> , 2005 , 133, 3-18	1.6	123
162	Light scattering by free carrier excitations in semiconductors. <i>Topics in Applied Physics</i> , 1984 , 5-150	0.5	123

161	Ultraviolet Reflection Spectrum of Cubic CdS. <i>Physical Review</i> , 1965 , 140, A633-A637		123
160	Angle-resolved uv photoemission and electronic band structures of the lead chalcogenides. <i>Physical Review B</i> , 1978 , 18, 3847-3871	3-3	119
159	Microscopic theory of intervalley scattering in GaAs: k dependence of deformation potentials and scattering rates. <i>Journal of Applied Physics</i> , 1990 , 68, 1682-1693	2-5	114
158	Raman spectroscopy of vibrations in superlattices 1989 , 49-152		113
157	Resonant First- and Second-Order Raman Scattering in GaP. <i>Physical Review B</i> , 1973 , 8, 2795-2809	3-3	111
156	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review Letters</i> , 1965 , 15, 883-885	7-4	103
155	Temperature Coefficient of the Refractive Index of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1970 , 2, 3193-3197	3-3	101
154	Isotope and temperature shifts of direct and indirect band gaps in diamond-type semiconductors. <i>Physical Review B</i> , 1992 , 45, 3376-3385	3-3	100
153	Second-Order Raman Spectrum of Germanium. <i>Physical Review B</i> , 1973 , 7, 2545-2551	3-3	96
152	Reflectivity of Gray Tin Single Crystals in the Fundamental Absorption Region. <i>Physical Review</i> , 1962 , 125, 1291-1296		94
151	Resonant Raman scattering in germanium. <i>Solid State Communications</i> , 1972 , 10, 591-595	1-6	86
150	Effect of Temperature and Doping on the Reflectivity of Germanium in the Fundamental Absorption Region. <i>Physical Review</i> , 1961 , 122, 1382-1388		85
149	Dependence of the indirect energy gap of silicon on hydrostatic pressure. <i>Solid State Communications</i> , 1975 , 17, 1021-1024	1-6	83
148	Infrared Dielectric Constant and Ultraviolet Optical Properties of Solids with Diamond, Zinc Blende, Wurtzite, and Rocksalt Structure. <i>Journal of Applied Physics</i> , 1965 , 36, 2181-2186	2-5	83
147	New Evidence for the Existence of Exciton Effects at Hyperbolic Critical Points. <i>Physical Review</i> , 1968 , 174, 828-830		81
146	Intervalley deformation potentials and scattering rates in zinc blende semiconductors. <i>Applied Physics Letters</i> , 1989 , 54, 614-616	3-4	79
145	Temperature dependence of the optical phonons and transverse effective charge in 3C-SiC. <i>Physical Review B</i> , 1982 , 25, 3889-3896	3-3	79
144	Photoluminescence in heavily doped GaAs. II. Hydrostatic pressure dependence. <i>Physical Review B</i> , 1980 , 22, 894-903	3-3	76

143	Self-energy effects of the optical phonons of heavily doped pGaAs and pTe. <i>Physical Review B</i> , 1981 , 23, 6592-6602	3.3	76
142	Interaction between electronic and vibronic Raman scattering in heavily doped silicon. <i>Solid State Communications</i> , 1973 , 13, 325-328	1.6	76
141	Isotopic effects on the lattice constant in compound semiconductors by perturbation theory: An ab initio calculation. <i>Physical Review B</i> , 1996 , 54, 11305-11310	3.3	74
140	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. <i>Physical Review B</i> , 1993 , 48, 7915-7929	3.3	73
139	Infrared absorption in hydrogenated amorphous and crystallized germanium. <i>Journal of Non-Crystalline Solids</i> , 1979 , 32, 421-430	3.9	72
138	Temperature dependence of the dielectric function and the interband critical-point parameters of GaSb. <i>Physical Review B</i> , 1991 , 43, 4349-4360	3.3	70
137	Resonance Raman scattering by LO phonons in Cd _x Hg _{1-x} Te at the E ₀ + Δ ₀ gap. <i>Physical Review B</i> , 1985 , 31, 3705-3711	3.3	69
136	Temperature dependence of the energy gap of semiconductors in the low-temperature limit. <i>Physical Review Letters</i> , 2004 , 92, 196403	7.4	68
135	The dielectric function of AlSb from 1.4 to 5.8 eV determined by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1989 , 66, 383-387	2.5	65
134	Energy-Band Structure and Optical Spectrum of Grey Tin. <i>Physical Review B</i> , 1970 , 2, 352-363	3.3	64
133	Resonant Raman scattering and interference effects of LO phonons at the E ₀ + Δ ₀ gap of InP. <i>Physical Review B</i> , 1986 , 33, 5473-5481	3.3	63
132	Excitons at the L Absorption Edge in Zinc Blende-Type Semiconductors. <i>Physical Review Letters</i> , 1962 , 8, 90-91	7.4	62
131	Evidence for Normal Regions at Low Temperatures in the Superconducting Mixed State. <i>Physical Review Letters</i> , 1964 , 12, 657-659	7.4	62
130	Effects of isotopic composition on the lattice dynamics of CuCl. <i>Physical Review B</i> , 1997 , 56, 210-220	3.3	59
129	Isotopic mass and lattice constant: X-ray standing wave measurements. <i>Science</i> , 1998 , 282, 930-2	33.3	59
128	Effect of hydrostatic pressure on the direct absorption edge of germanium. <i>Physical Review B</i> , 1977 , 15, 875-879	3.3	59
127	Spatial dispersion in the dielectric constant of GaAs. <i>Solid State Communications</i> , 1971 , 9, 1421-1424	1.6	58
126	Intraband Raman scattering by free carriers in heavily doped nBi. <i>Physical Review B</i> , 1977 , 16, 3579-3595	3.3	57

125	Valence Band Structure of PbS from Angle-Resolved Photoemission. <i>Physical Review Letters</i> , 1977 , 38, 1033-1036	7.4	54
124	Optical Properties of Some Compound Semiconductors in the 36-150-eV Region. <i>Physical Review B</i> , 1970 , 1, 2605-2612	3.3	53
123	Valence band symmetry and deformation potentials of ZnO. <i>Solid State Communications</i> , 1968 , 6, 239-242		53
122	Electroreflectance Measurements on Mg ₂ Si, Mg ₂ Ge, and Mg ₂ Sn. <i>Physical Review</i> , 1968 , 176, 905-908		53
121	Interference between Allowed and Forbidden Raman Scattering by Longitudinal-Optical Phonons in GaAs. <i>Physical Review Letters</i> , 1983 , 51, 1297-1299	7.4	51
120	Optical Studies of the Band Structure of InP. <i>Journal of Applied Physics</i> , 1961 , 32, 958-958	2.5	50
119	Reflectivity of Semiconductors with Wurtzite Structure. <i>Physical Review</i> , 1963 , 129, 1068-1069		50
118	Transverse electroreflectance in semi-insulating silicon and gallium arsenide. <i>Journal of Physics and Chemistry of Solids</i> , 1970 , 31, 227-246	3.9	49
117	The temperature dependence of the band gaps in InP, InAs, InSb, and GaSb. <i>Solid State Communications</i> , 1991 , 77, 485-488	1.6	48
116	Stress-Induced Exchange Splitting of Hyperbolic Excitons in GaAs. <i>Physical Review Letters</i> , 1969 , 22, 933-936	7.4	48
115	Piezobirefringence and Deformation Potentials of the Alkali Halides. <i>Physical Review</i> , 1969 , 177, 1351-1357		47
114	Raman scattering in high T _c superconductors: phonons, electrons, and electron-phonon interaction. <i>Physica C: Superconductivity and Its Applications</i> , 1999 , 317-318, 30-54	1.3	46
113	Dependence of the direct energy gap of GaP on hydrostatic pressure. <i>Solid State Communications</i> , 1985 , 55, 327-331	1.6	46
112	Light scattering as a form of modulation spectroscopy. <i>Surface Science</i> , 1973 , 37, 100-119	1.8	46
111	Piezoelectroreflectance in GaAs. <i>Physical Review Letters</i> , 1966 , 16, 942-944	7.4	46
110	Strain dependence of effective masses in tetrahedral semiconductors. <i>Physical Review B</i> , 1978 , 17, 726-740	3.9	45
109	Raman scattering by electronic excitations in semiconductors and in high T _c superconductors. <i>Journal of Low Temperature Physics</i> , 1995 , 99, 205-221	1.3	44
108	Electroreflectance and Spin-Orbit Splitting in III-V Semiconductors. <i>Physical Review Letters</i> , 1966 , 16, 48-50	7.4	43

107	Resonant spin-flip Raman scattering on donor and acceptor states in ZnTe. <i>Physical Review B</i> , 1981 , 23, 4129-4139	3.3	41
106	Deformation Potentials of the Indirect and Direct Absorption Edges of AlSb. <i>Physical Review B</i> , 1970 , 1, 1436-1442	3.3	40
105	Piezoresistance and the conduction-band minima of GaAs. <i>Physical Review B</i> , 1978 , 17, 741-751	3.3	39
104	Effect of isotope substitution and doping on the Raman spectrum of galena (PbS). <i>Solid State Communications</i> , 2005 , 134, 565-570	1.6	38
103	Polarization effects in the ultraviolet reflection of crystals with wurtzite structure. <i>Solid State Communications</i> , 1963 , 1, 109-115	1.6	38
102	Electroreflectance and band structure of gray tin. <i>Solid State Communications</i> , 1966 , 4, 319-321	1.6	38
101	Two-phonon Raman spectra of Si and GaP. <i>Solid State Communications</i> , 1972 , 10, 961-965	1.6	36
100	Infrared absorption in amorphous silicon from ab initio molecular dynamics. <i>Applied Physics Letters</i> , 1997 , 71, 2692-2694	3.4	35
99	Phonons, Strains, and Pressure in Semiconductors. <i>Semiconductors and Semimetals</i> , 1998 , 55, 117-233	0.6	35
98	Valence bands of the Mg ₂ X(X=Si, Ge, Sn) semiconducting compounds. <i>Physical Review B</i> , 1976 , 14, 2559-2568	3.3	35
97	Electroreflectance in AlSb: Observation of the Direct Band Edge. <i>Physical Review Letters</i> , 1966 , 16, 644-646	1.6	35
96	X ₁ and X ₃ states of electrons and phonons in zincblende type semiconductors. <i>Solid State Communications</i> , 1988 , 67, 927-930	1.6	33
95	Resonant Raman scattering by plasmons and LO phonons near the E ₁ and E ₁ +Δ ₁ gaps of GaSb. <i>Physical Review B</i> , 1987 , 36, 7469-7485	3.3	32
94	Photorefectance and electroreflectance in silicon. <i>Solid State Communications</i> , 1969 , 7, 879-882	1.6	32
93	Energy band structure of germanium and gallium arsenide: The π method. <i>Journal of Physics and Chemistry of Solids</i> , 1966 , 27, 423-425	3.9	32
92	Transverse reduced mass of the E ₁ and E ₁ + π transitions in silicon. <i>Physical Review B</i> , 1977 , 15, 5999-6000	3.3	31
91	Electron-phonon interaction at the direct gap of the copper halides. <i>Solid State Communications</i> , 1996 , 98, 27-30	1.6	30
90	Resonant Raman scattering in the II-IV semiconductors Mg ₂ Si, Mg ₂ Ge, and Mg ₂ Sn. <i>Physical Review B</i> , 1976 , 14, 3520-3531	3.3	30

89	Comment on "Spectroscopy of excited states in In _{0.53} Ga _{0.47} As-InP single quantum wells grown by chemical-beam epitaxy". <i>Physical Review B</i> , 1988 , 37, 1011-1012	3.3	29
88	X-ray and far ultraviolet photoemission of AlSb. <i>Solid State Communications</i> , 1972 , 11, 1619-1623	1.6	29
87	Resonances of a Small Plasma Sphere in a Magnetic Field. <i>Physical Review</i> , 1963 , 129, 991-997		29
86	Effect of heavy doping on the optical properties and band structure of GaAs. <i>Physical Review B</i> , 1993 , 47, 7071-7079	3.3	27
85	Optical investigation of the band structure of GaSb. <i>European Physical Journal A</i> , 1961 , 161, 99-102	2.5	27
84	Electronic surface states in germanium and silicon. <i>Solid State Communications</i> , 1966 , 4, 271-274	1.6	27
83	Vibrational spectra of a-Si: H, a-Si: F, and a-Ge: F: Bethe-lattice calculations. <i>Physical Review B</i> , 1983 , 28, 880-888	3.3	26
82	Correlation between the Josephson coupling energy and the condensation energy in bilayer cuprate superconductors. <i>Physical Review B</i> , 2001 , 64,	3.3	25
81	Raman scattering by two LO-phonons near $\bar{\Gamma}$ in GaAs. <i>Solid State Communications</i> , 1981 , 39, 1071-1075	1.6	25
80	Optical constants of germanium and gray tin the . method. <i>Solid State Communications</i> , 1967 , 5, 513-516	1.6	25
79	Raman scattering in high-T _c superconductors. <i>Physica C: Superconductivity and Its Applications</i> , 1991 , 185-189, 65-71	1.3	24
78	Microwave Surface Impedance of Superconductors of the Second Kind: In-Bi Alloys. <i>Physical Review Letters</i> , 1964 , 12, 101-103	7.4	24
77	Optical Constants of Insulators: Dispersion Relations 1969 , 137-151		23
76	Electronic properties of clean and oxygen covered (100) cleaved surfaces of PbS. <i>Surface Science</i> , 1980 , 92, 385-392	1.8	22
75	Derivative spectrum of indirect excitons in AlSb. <i>Solid State Communications</i> , 1969 , 7, 441-444	1.6	22
74	Modulation Spectroscopy of Semiconductors 1970 , 125-173		22
73	Are transverse phonons important for \bar{X} -intervalley scattering?. <i>Solid-State Electronics</i> , 1989 , 32, 1585-1589		21
72	Effect of free carriers on the elastic constants of p-type silicon and germanium. <i>Physical Review B</i> , 1976 , 13, 5429-5441	3.3	21

71	Effects of Free Carriers on Zone-Center Vibrational Modes in Heavily Doped p-type Si. I. Acoustical Modes. <i>Physical Review B</i> , 1973 , 8, 4723-4733	3.3	21
70	Path-integral molecular dynamics simulation of 3CβiC. <i>Physical Review B</i> , 2008 , 77,	3.3	20
69	Effective intervalley deformation potentials in the description of time-resolved and hot-electron luminescence. <i>Solid State Communications</i> , 1990 , 76, 877-879	1.6	20
68	Resonant Raman scattering by LO phonons near the E0+ Delta 0 gap of GaSb. <i>Physical Review B</i> , 1987 , 35, 9619-9624	3.3	20
67	Band structure of gray tin under uniaxial stress. <i>Solid State Communications</i> , 1967 , 5, 233-235	1.6	20
66	First principles calculation of the real part of phonon self energy in compound semiconductors. <i>Physica B: Condensed Matter</i> , 1999 , 263-264, 687-690	2.8	19
65	Electronic Raman scattering in heavily doped p-type germanium. <i>Physical Review B</i> , 1985 , 32, 8071-8077	3.3	18
64	Light scattering by plasmons in germanium. <i>Physical Review B</i> , 1984 , 29, 3737-3739	3.3	17
63	Intra- and inter-valence-band electronic Raman scattering in heavily doped p-GaAs. <i>Physical Review B</i> , 1980 , 22, 1905-1911	3.3	17
62	Full-zone analysis of relativistic spin splitting at band anticrossings: The case of zinc-blende semiconductors. <i>Physical Review B</i> , 2010 , 81,	3.3	16
61	Ultrafast initial relaxation of hot electrons and holes in tetrahedral semiconductors via deformation potential interaction: Theory and experiment. <i>Applied Physics Letters</i> , 1990 , 57, 2838-2840	3.4	16
60	Photoemission of GaAs and InSb core levels. <i>Solid State Communications</i> , 1972 , 11, 1655-1658	1.6	16
59	Microscopic theory of intervalley scattering in InP. <i>Physical Review B</i> , 1991 , 44, 13446-13451	3.3	15
58	Vibrations in amorphous silicon and its alloys. <i>Journal of Molecular Structure</i> , 1986 , 141, 93-107	3.4	15
57	Comment on "g-factor anisotropy of conduction electrons in InSb". <i>Physical Review B</i> , 1986 , 34, 7402-7403	3.3	15
56	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. <i>Thin Solid Films</i> , 1993 , 233, 185-188	2.2	14
55	Spin relaxation of holes in the split-hole band of InP and GaSb. <i>Physical Review B</i> , 1987 , 35, 3843-3853	3.3	14
54	Intrinsic piezobirefringence of AlSb. <i>Solid State Communications</i> , 1969 , 7, 1113-1117	1.6	14

53	Resonant Raman scattering in germanium and zincblende-type semiconductors temperature dependence. <i>Solid State Communications</i> , 1971 , 9, 1235-1238	1.6	14
52	Dependence of the excitation energies of boron in diamond on isotopic mass. <i>Solid State Communications</i> , 2001 , 121, 7-8	1.6	13
51	Self-consistent calculation of intervalley deformation potentials in GaAs and Ge. <i>Journal of Applied Physics</i> , 1993 , 74, 2117-2119	2.5	13
50	Thermoreflectance in the alkali metals. <i>Solid State Communications</i> , 1968 , 6, 313-316	1.6	13
49	The citation impact outside references [Formal versus informal citations. <i>Scientometrics</i> , 2009 , 80, 1-21	3	12
48	Variation of the Ratio Hc_3Hc_2 in the Immediate Vicinity of T_c . <i>Physical Review</i> , 1969 , 187, 766-767		12
47	Conduction-band minima of InP: Ordering and absolute energies. <i>Applied Physics Letters</i> , 1990 , 57, 2339-2341	3.4	11
46	Resonant Raman scattering by spin-density fluctuations in n-type germanium. <i>Physical Review Letters</i> , 1985 , 55, 1132-1135	7.4	11
45	Temperature effects on valence bands in semiconducting lead chalcogenides. <i>Solid State Communications</i> , 1979 , 32, 353-356	1.6	11
44	Ellipsometric investigations of piezo-optical effects. <i>Thin Solid Films</i> , 1998 , 313-314, 10-17	2.2	10
43	A new application of the diamond anvil cell: Measurements under uniaxial stress. <i>Solid State Communications</i> , 1981 , 38, 1109-1112	1.6	10
42	Temperature Dependence of the Band Structure of Semiconductors: Electron-Phonon Interaction. <i>Physics and Chemistry of Materials With Low-dimensional Structures</i> , 1989 , 51-64		10
41	Isotope effects on the lattice parameter of cubic SiC. <i>Physical Review B</i> , 2009 , 79,	3.3	8
40	Phonons in isotopically modified semiconductors and high T_c superconductors. <i>Physica B: Condensed Matter</i> , 1999 , 263-264, 376-380	2.8	8
39	Luminescence above the gap in heavily Zn-doped GaAs. <i>Solid State Communications</i> , 1979 , 32, 1027-1030	1.6	8
38	Modulation spectroscopy of semiconductors 1970 , 125-173		8
37	Intervalley scattering times from the rigid-pseudoion method 1990 , 1282, 78		7
36	Anomalous Behavior of Hc_3Hc_2 near T_c for Sn-In and In-Bi Alloy Systems. <i>Physical Review B</i> , 1970 , 2, 2513-2519	3.5	196

35	Elastic constants and Raman frequencies of heavily doped Si under uniaxial stress. <i>Solid State Communications</i> , 1973 , 12, 553-556	1.6	6
34	Chapter 5 Optical Absorption above the Fundamental Edge. <i>Semiconductors and Semimetals</i> , 1967 , 3, 125-151	0.6	6
33	The disaster of the Nazi-power in science as reflected by some leading journals and scientists in physics.. <i>Scientometrics</i> , 2005 , 64, 313-324	3	5
32	Optical Properties I 1996 , 233-331		5
31	Resonant Raman Scattering in Semiconductors. <i>Physica Scripta</i> , 1989 , T25, 201-205	2.6	5
30	Phonon anomalies in the far-infrared c-axis conductivity of underdoped YBa ₂ Cu ₃ O _y as Evidence for the intra-bilayer Josephson effect. <i>Journal of Low Temperature Physics</i> , 1999 , 117, 1049-1053	1.3	4
29	Electron-phonon interaction and phonon softening in ferro-electrics and semiconductors. <i>Ferroelectrics</i> , 1984 , 53, 49-58	0.6	4
28	Optical Properties I 1999 , 233-331		4
27	Optical Properties I. <i>Graduate Texts in Physics</i> , 2005 , 243-343	0.3	3
26	Alloy versus phonon contributions to intervalley scattering in Al _{1-x} Ga _x As 1992 , 1677, 75		3
25	Linear optical response of semiconductors. <i>Journal of Electronic Materials</i> , 1993 , 22, 27-37	1.9	3
24	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions 1999 , 99-147		3
23	Optical Properties II. <i>Graduate Texts in Physics</i> , 2005 , 345-426	0.3	2
22	Phonons, Electrons, and Electron-Phonon Interaction: Semiconductors and High-T _c Superconductors 2002 , 257-293		2
21	Optical constants of pure and heavily doped silicon and germanium: Electronic interband transitions. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983 , 117-118, 356-358		2
20	Resonant Raman scattering by plasmons in n-type Ge. <i>Solid State Communications</i> , 1984 , 49, 1103-1105	1.6	2
19	Optical Properties II 1999 , 333-413		2
18	On the value of author indices. <i>Physics Today</i> , 2011 , 64, 9-10	0.9	1

17	Light emission at the E1 and E1+ Γ gaps in heavily doped p-type Ge and GaAs. <i>Solid State Communications</i> , 1985 , 56, 549-552	1.6	1
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